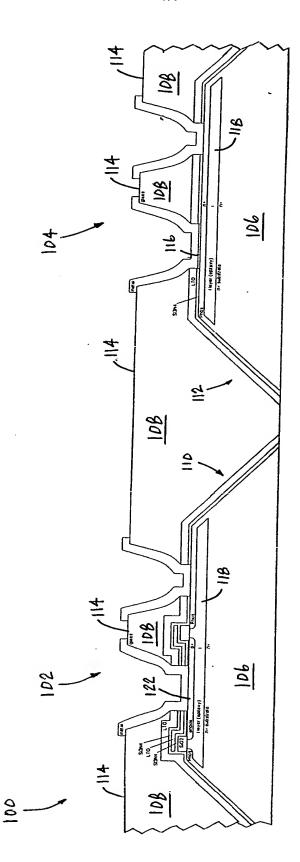
Title: MONOLITHICALLY INTEGRATED PIN DIODE AND SCHOTTKY DIODE CIRCUIT AND METHOD OF FABRICATING SAME

Inventor Name: James J. Brogle

Appl. No. Unassigned Docket No.: TYCO-017XX

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Title: MONOLITHICALLY INTEGRATED DIODE AND SCHOTTKY DIODE CIRCUIT METHOD OF FABRICATING SAME Inventor Name: James J. Brogle

Appl. No. Unassigned Docket No.: TYCO-017XX

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102.1

y>

LTO 128 Si3N4 126 124 122 120 120 IIB i layer (epitaxy) n+ substrate 106

Fig. 2a

104.1 LTO 128 _SI3N4 126 SiO2 120 I layer (epitaxy) 118 nt substrate 106

Fig. 2b

Title: MONOLITHICALLY INTEGRATED DIODE AND SCHOTTKY DIODE CIRCUIT METHOD OF FABRICATING SAME Inventor Name: James J. Brogle

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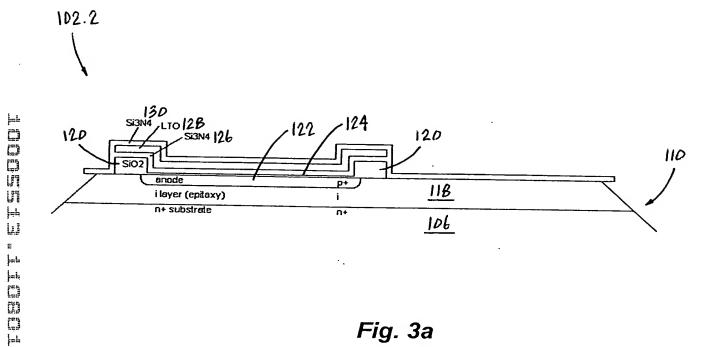


Fig. 3a

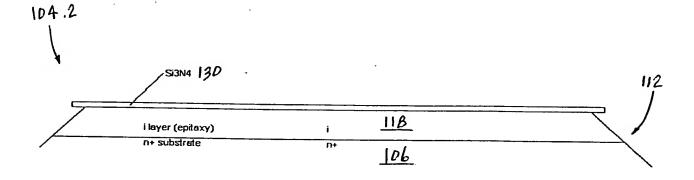


Fig. 3b

Title: MONOLITHICALLY INTEGRATE DIODE AND SCHOTTKY DIODE CIRCUI METHOD OF FABRICATING SAME Inventor Name: James J. Brogle

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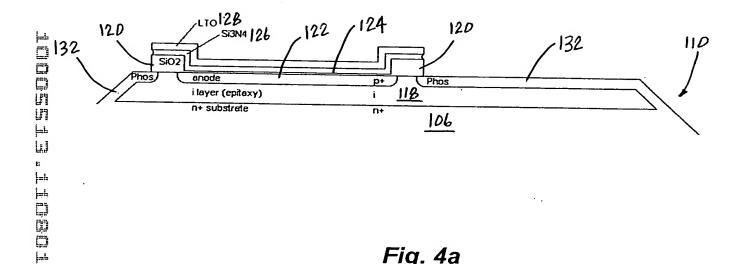


Fig. 4a

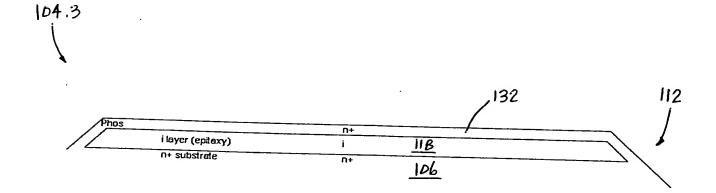
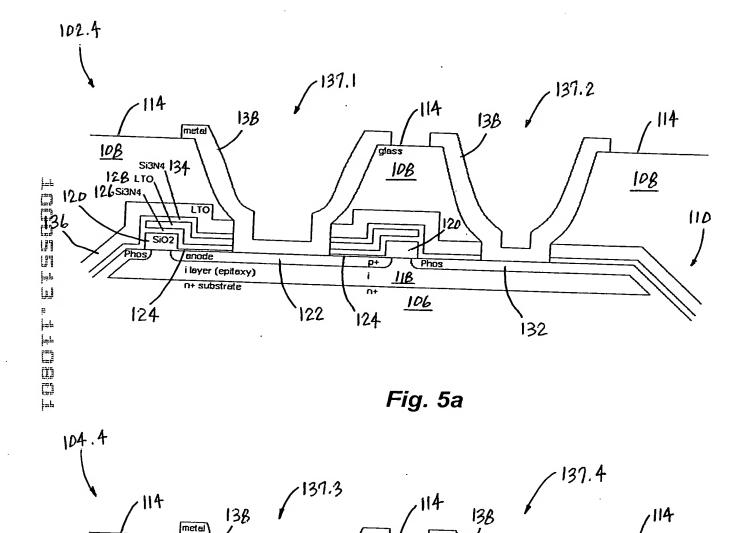


Fig. 4b

Title: MONOLITHICALLY INTEGRATED DIODE AND SCHOTTKY DIODE CIRCUIT METHOD OF FABRICATING SAME Inventor Name: James J. Brogle

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glass

n epitexy

116

IDB

Phos

136

Si3N4, 134

LTO

i layer (epitaxy)

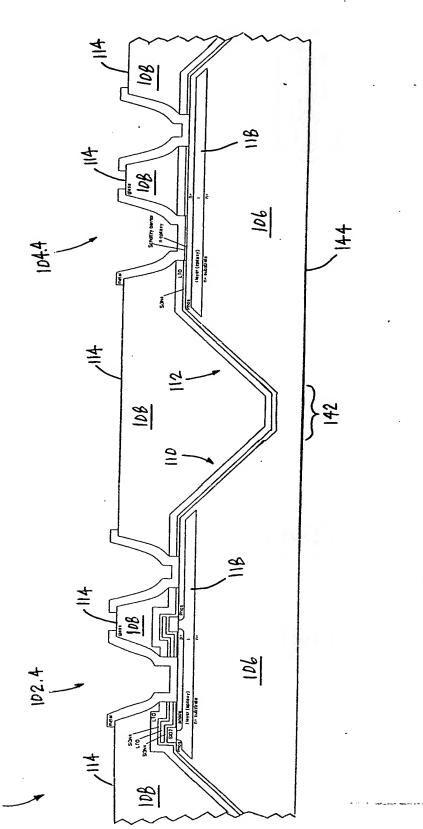
n+ substrate

IDB 108 140 Schottky barrier 112 n+ 118 106 132

Fig. 5b

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